First Named Inventor	Leonard Forbes	
Serial No.	10/612,725	
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Group Art Unit	2811 2815	
Examiner Name	Unknown	
Confirmation No.	5767	
Attorney Docket No.	400.258US01	
Title: APPARATUS A TRANSISTOR MEMO		

Examiner

## INFORMATION DISCLOSURE **STATEMENT FORM PTO-1449**

SPLIT OVED **ENDURANCE** 

Sheet 1 of 7

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First Named Inventor	Leonard Forbes
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10/612,725
July 1, 2003
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Title: APPARATUS AND METHOD FOR SPLIT TRANSISTOR MEMORY HAVING IMPROVED **ENDURANCE** 

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Title: APPARATUS AND METHOD FOR SPLIT TRANSISTOR MEMORY HAVING IMPROVED **ENDURANCE** 

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## INFORMATION DISCLOSURE STATEMENT FORM PTO-1449

Title: APPARATUS AND METHOD FOR SPLIT TRANSISTOR MEMORY HAVING IMPROVED ENDURANCE Sheet 6 of 7

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